

WSP6039

**P-Ch MOSFET** 

#### **General Description**

The WSP6039 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP6039 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

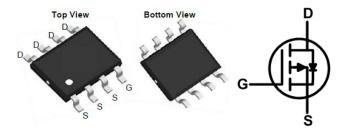
## **Product Summery**

BVDSS	RDSON	ID
-60V	88mΩ	-3.5A

#### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

#### **SOP-8 Pin Configuration**



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	-60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current	-3.5	А	
I <sub>D</sub> @T <sub>C</sub> =70℃	Continuous Drain Current	-2.5	А	
I <sub>DP</sub>	Pulsed Drain Current	-17.5	А	
P₀@T₀=25℃	Total Power Dissipation	2.0	W	
T <sub>J</sub> /T <sub>STG</sub>	Operating/Storage Temperature Range	-55 to 150	°C	

## **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit	
R <sub>0JA</sub>	Thermal Resistance Junction-Ambient			°C/W	
R <sub>eJC</sub>	Thermal Resistance Junction-Case		4	°C/W	



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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V
Б	Statia Drain Source On Desistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-4A		88	114	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A		118	153	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_{D}=-250 uA$	-1.0	-1.65	-3.0	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-60V , V <sub>GS</sub> =0V			-1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm20V$ , $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge (-4.5V)	VDS = -30V, ID = -3.7A,		17		
Q <sub>gs</sub>	Gate-Source Charge	VGS = -10V		2		nC
$Q_gd$	Gate-Drain Charge			4		
T <sub>d(on)</sub>	Turn-On Delay Time			11		
Tr	Rise Time	VDD = -30V, ID = -1A,		4.5		ns
T <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = -10V, $R_{GEN}$ = 6 $\Omega$		50		115
T <sub>f</sub>	Fall Time			15		
C <sub>iss</sub>	Input Capacitance			615		
C <sub>oss</sub>	Output Capacitance	VDS = -30V, VGS = 0V,f = 1.0 MHz		140		рF
C <sub>rss</sub>	Reverse Transfer Capacitance			45		

# P-Channel Electrical Characteristics (T<sub>J</sub>=25<sup>-1</sup>C, unless otherwise noted)

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	$V_G = V_D = 0V$ , Force Current			-3.5	А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}$ =0V , $I_{S}$ =-1A , $T_{J}$ =25 $^{\circ}$ C			-1.2	V

A: The value of R BJA is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given

application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

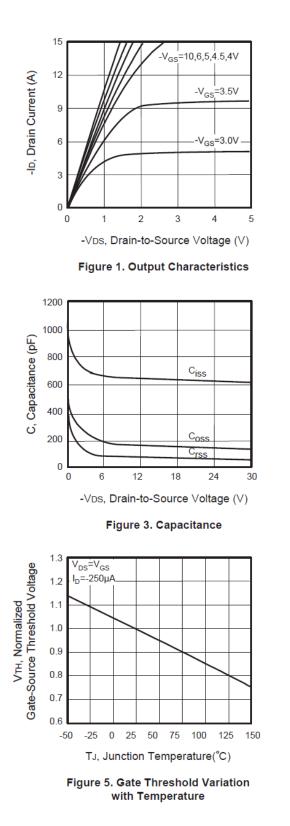
C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating



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# **P-Channel Typical Characteristics**



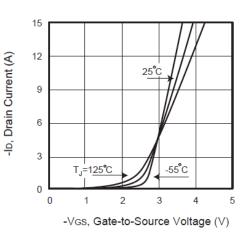


Figure 2. Transfer Characteristics

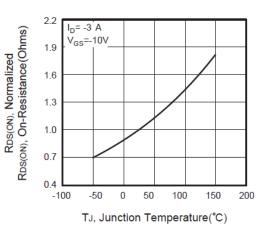


Figure 4. On-Resistance Variation with Temperature

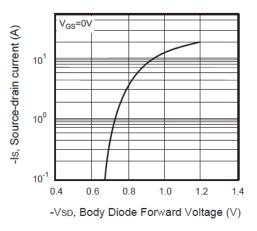
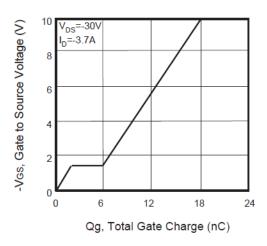


Figure 6. Body Diode Forward Voltage Variation with Source Current

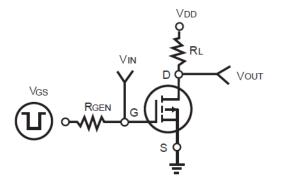


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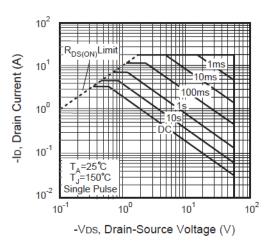
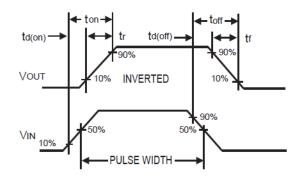


Figure 8. Maximum Safe Operating Area





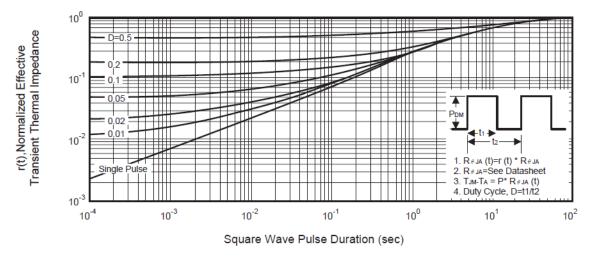


Figure 11. Normalized Thermal Transient Impedance Curve



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